

APM2300CA

N-Channel Enhancement Mode MOSFET

Features

- 20V/6A ,
 $R_{DS(ON)} = 25m\Omega$ (typ.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 32m\Omega$ (typ.) @ $V_{GS} = 4.5V$
 $R_{DS(ON)} = 40m\Omega$ (typ.) @ $V_{GS} = 2.5V$
 $R_{DS(ON)} = 65m\Omega$ (typ.) @ $V_{GS} = 1.8V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

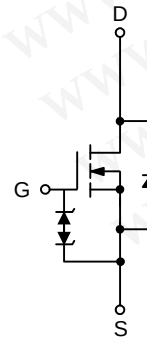
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description



Top View of SOT-23



N-Channel MOSFET

Ordering and Marking Information

APM2300C □□-□□□ Lead Free Code Handling Code Temp. Range Package Code	Package Code A : SOT-23 Operating Junction Temp. Range C : -55 to 150 °C Handling Code TR : Tape & Reel Lead Free Code L : Lead Free Device
APM2300C A : C00X	X - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte in plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±12	
I _D *	Continuous Drain Current	V _{GS} =10V	6	A
I _{DM} *	300μs Pulsed Drain Current		20	
I _S *	Diode Continuous Forward Current		1	A
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
P _D *	Maximum Power Dissipation	T _A =25°C	0.83	W
		T _A =100°C	0.3	
R _{θJA} *	Thermal Resistance-Junction to Ambient		150	°C/W

Notes:

*Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics $(T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM2300CA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	0.75	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V			±10	μA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =6A		25	30	mΩ
		V _{GS} =4.5V, I _{DS} =3A		32	40	
		V _{GS} =2.5V, I _{DS} =2A		40	55	
		V _{GS} =1.8V, I _{DS} =1A		65	110	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V		0.7	1.3	V
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =6A		6	8	nC
Q _{gs}	Gate-Source Charge			0.7		
Q _{gd}	Gate-Drain Charge			3		

Electrical Characteristics (Cont.) (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	APM2300CA			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		6		Ω
C _{iSS}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz		430		pF
C _{oSS}	Output Capacitance			110		
C _{rSS}	Reverse Transfer Capacitance			90		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω		5	10	ns
t _r	Turn-on Rise Time			15	28	
t _{d(OFF)}	Turn-off Delay Time			26	48	
t _f	Turn-off Fall Time			15	28	
t _{rr}	Reverse Recovery Time	I _{SD} =6A, dI _{SD} /dt=100A/μs		21		ns
Q _{rr}	Reverse Recovery Charge			8		nC

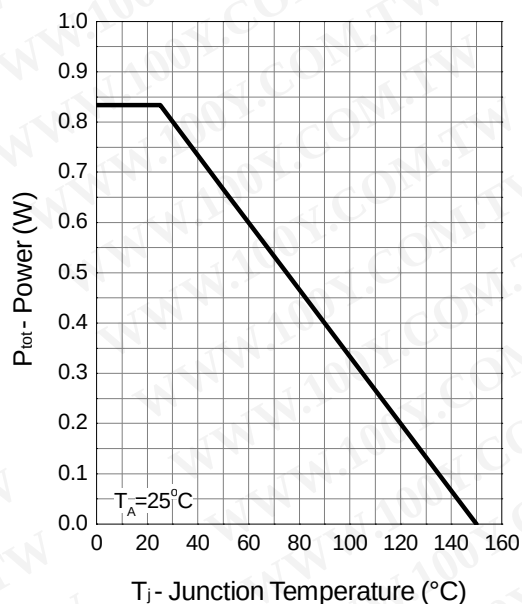
Notes:

a : Pulse test ; pulse width≤300μs, duty cycle≤2%.

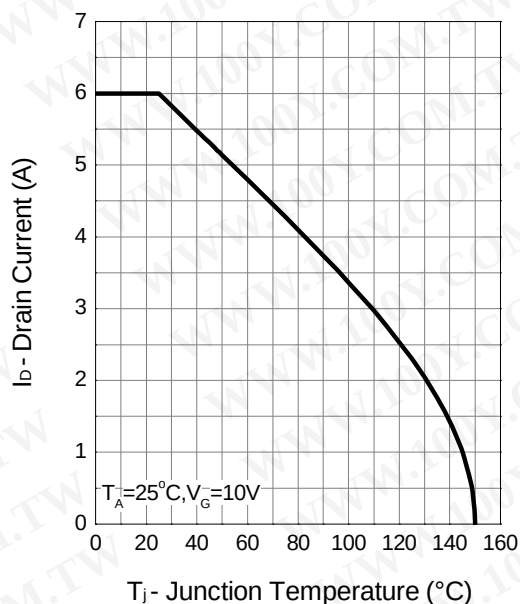
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

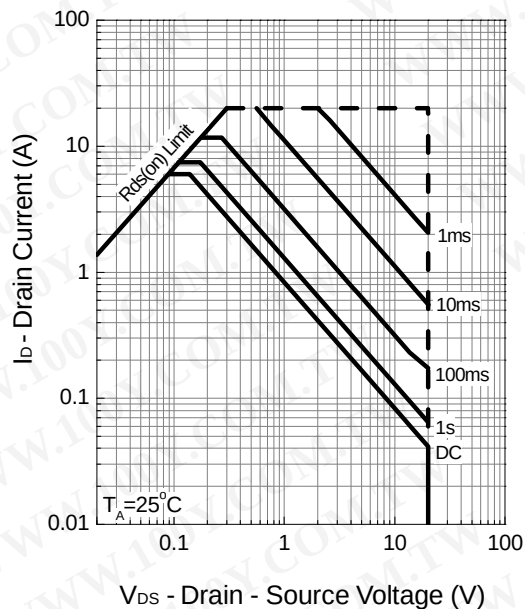
Power Dissipation



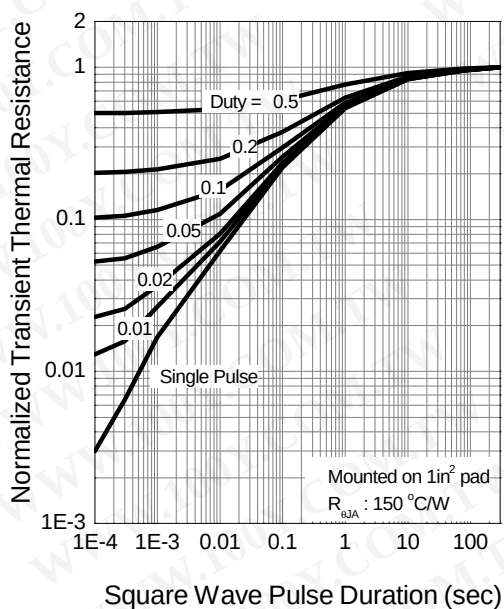
Drain Current



Safe Operation Area

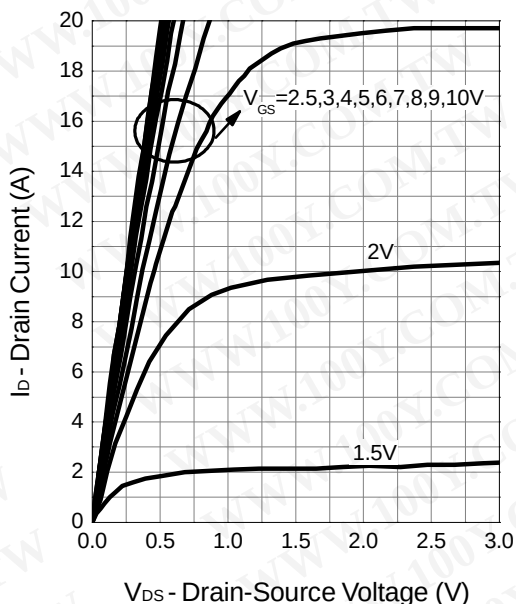


Thermal Transient Impedance

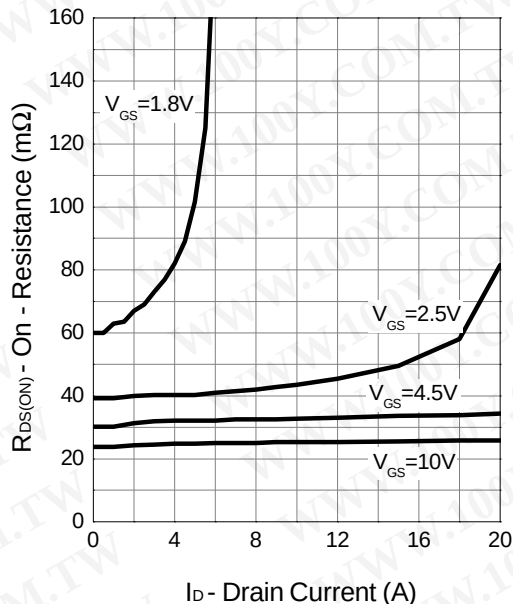


Typical Characteristics (Cont.)

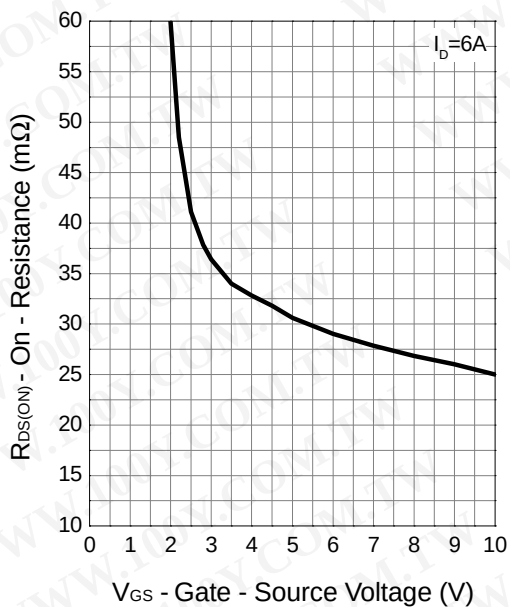
Output Characteristics



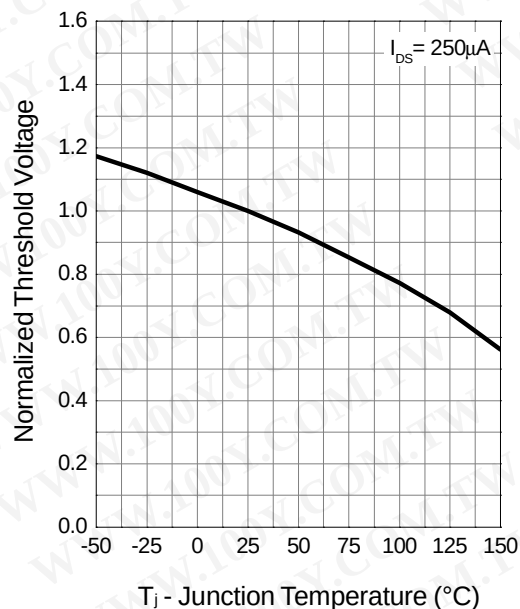
Drain-Source On Resistance



Drain-Source On Resistance

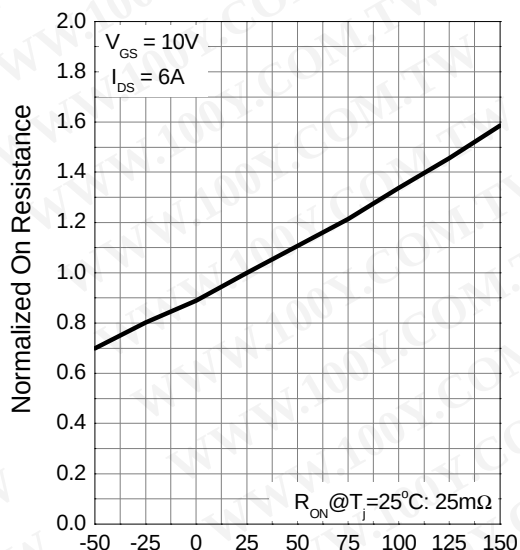


Gate Threshold Voltage



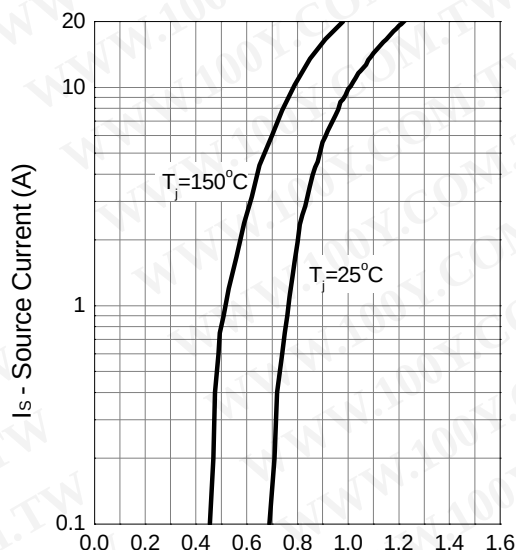
Typical Characteristics (Cont.)

Drain-Source On Resistance



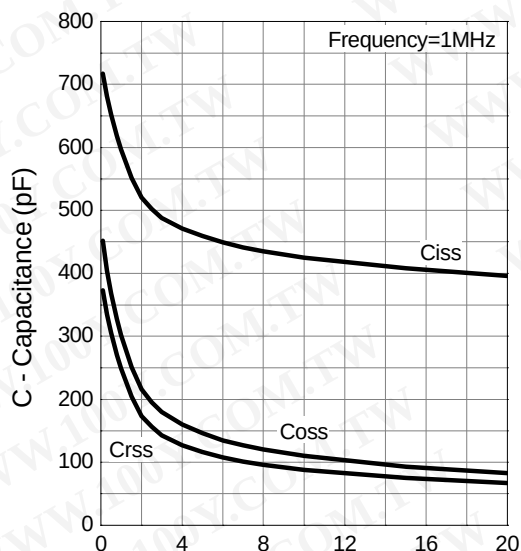
T_j - Junction Temperature ($^\circ C$)

Source-Drain Diode Forward



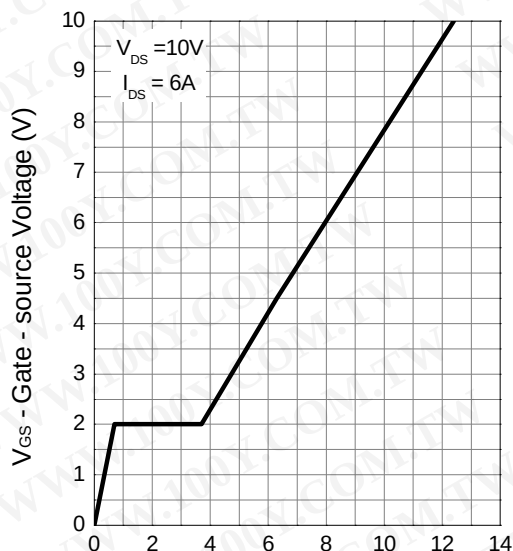
V_{SD} - Source - Drain Voltage (V)

Capacitance



V_{DS} - Drain - Source Voltage (V)

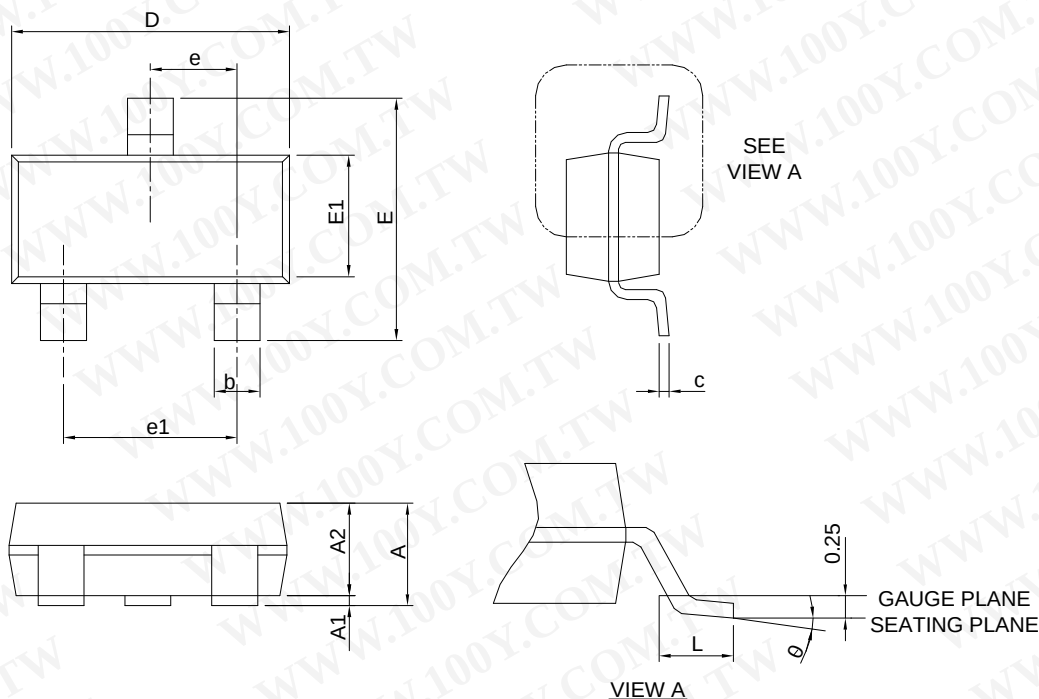
Gate Charge



Q_G - Gate Charge (nC)

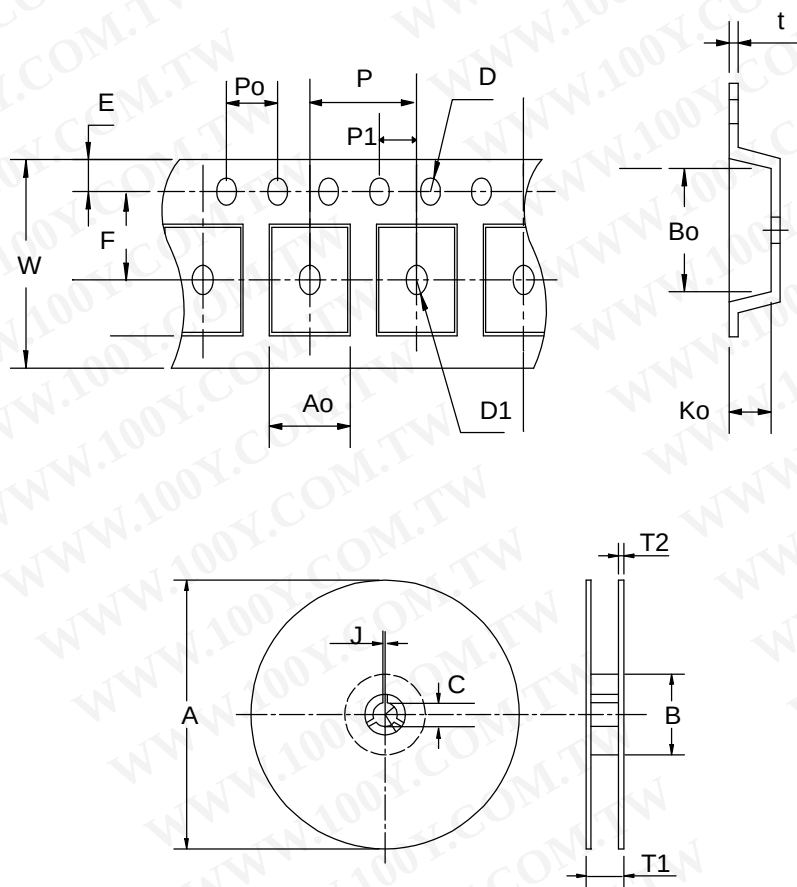
Packaging Information

SOT23-3



SYMBOL	SOT23-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.45		0.057
A1	0.00	0.15	0.000	0.006
A2	0.90	1.30	0.035	0.051
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.90 BSC		0.114 BSC	
E	2.80 BSC		0.110 BSC	
E1	1.60 BSC		0.063 BSC	
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOT-23	178±1	60 ± 1.0	12.0	2.5 ± 0.15	9.0 ± 0.5	1.4	8.0+0.3 -0.3	4.0	1.75
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	3.5 ± 0.05	1.5 +0.1	φ0.1MIN	4.0	2.0 ± 0.05	3.1	3.0	1.3	0.2±0.03

(mm)

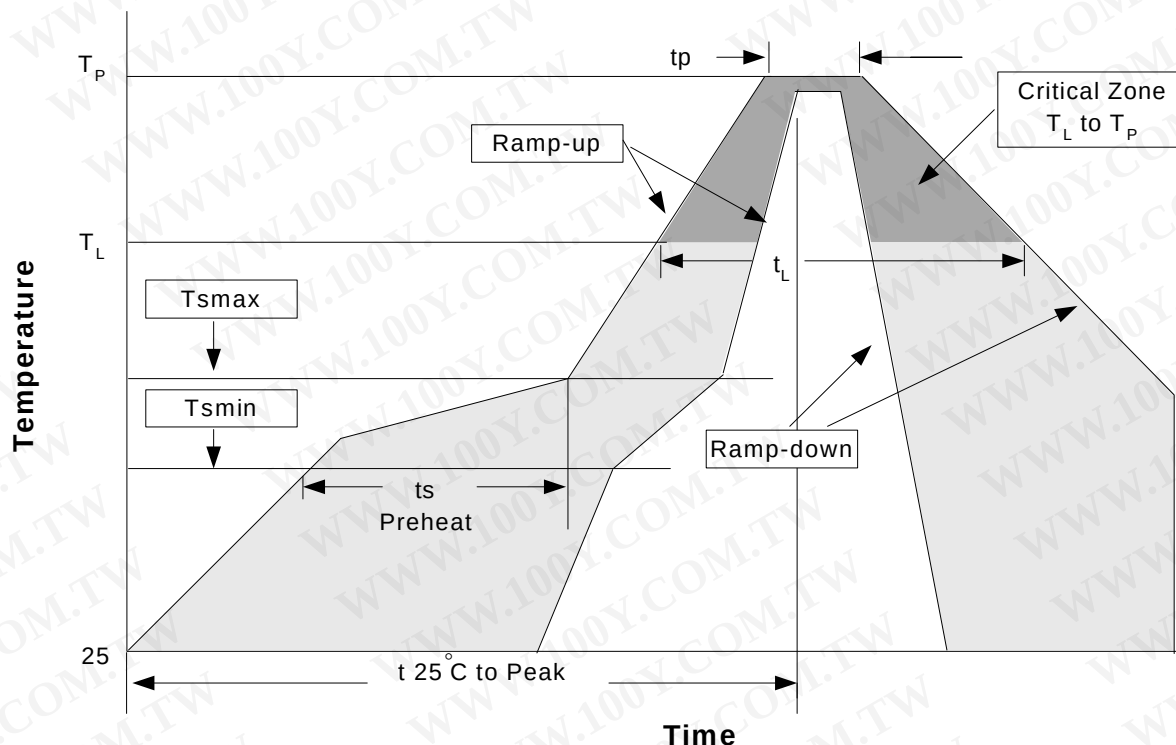
Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOT- 23	8	5.3	3000

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (Tsmin) - Temperature Max (Tsmax) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (Tp)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥ 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Customer Service

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